SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

Abstract of Disclosure

A method for fabricating a semiconductor device includes the steps of first providing a substrate having a transistor region and an one time programmable (OTP) capacitor region, forming a first fin-shaped structure on the transistor region and a second fin-shaped structure on the OTP capacitor region, and then performing an oxidation process to form a gate oxide layer on the first fin-shaped structure and the second fin-shaped structure. Preferably, the first fin-shaped structure and the second fin-shaped structure have different shapes under a cross-section perspective.

Figure 1